

International
IOR Rectifier

100BGQ045
100BGQ045J

SCHOTTKY RECTIFIER

100 Amp

Major Ratings and Characteristics

Characteristics	100BGQ045	Units
$I_{F(AV)}$ Rectangular waveform	100	A
@ T_C	100	°C
I_{DC} Maximum	141	A
V_{RRM}	45	V
I_{FSM} @ $t_p = 5 \mu s$ sine	4400	A
V_F @100Apk typical	0.63	V
@ T_J	150	°C
T_J range	-55 to 150	°C

Description/ Features

The 100BGQ045 Schottky rectifier has been optimized for ultra low forward voltage drop specifically for low voltage output in high current AC/DC power supplies.

The proprietary barrier technology allows for reliable operation up to 150°C junction temperature. Typical applications are in switching power supplies, converters, reverse battery protection, and redundant power subsystems.

- 150°C T_J operation
- High Frequency Operation
- Ultra low forward voltage drop
- Continuous High Current operation
- Guard ring for enhanced ruggedness and long term reliability
- **PowIRtab™ package**

Case Styles

100BGQ045



100BGQ045J



100BGQ045, 100BGQ045J

Bulletin PD-20709 rev. D 12/02

International
IR Rectifier

Voltage Ratings

Part number	100BGQ045
V_R Max. DC Reverse Voltage (V)	45
V_{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters	100BGQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current	100	A	50% duty cycle @ $T_C = 100^\circ\text{C}$, rectangular wave form
$I_{F(RMS)}$ RMS Forward Current	141	A	$T_C = 95^\circ\text{C}$
I_{FSM} Max. Peak One Cycle Non-Repetitive Surge Current	4400	A	5 μs Sine or 3 μs Rect. pulse
	830		10ms Sine or 6ms Rect. pulse
E_{AS} Non-Repetitive Avalanche Energy	40	mJ	Following any rated load condition and with rated V_{RWM} applied
I_{AR} Repetitive Avalanche Current	6	A	$T_J = 25^\circ\text{C}$, $I_{AS} = 6\text{ Amps}$, $L = 2.0\text{ mH}$
			Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	100BGQ		Units	Conditions	
	Typ.	Max.			
V_{FM} Forward Voltage Drop (1) (2)	0.52	0.56	V	@ 50A	$T_J = 25^\circ\text{C}$
	0.67	0.73	V	@ 100A	
	0.47	0.52	V	@ 50A	$T_J = 150^\circ\text{C}$
	0.63	0.68	V	@ 100A	
I_{RM} Reverse Leakage Current (1)	0.3	1	mA	$T_J = 25^\circ\text{C}$	$V_R = \text{rated } V_R$
	180	320	mA	$T_J = 125^\circ\text{C}$	
	600	1000	mA	$T_J = 150^\circ\text{C}$	
$V_{F(TO)}$ Threshold Voltage	0.379		V	$T_J = T_J \text{ max.}$	$V_R = 45\text{ V}$
r_t Forward Slope Resistance	2.7		m Ω		
C_T Max. Junction Capacitance	2700		pF	$V_R = 5V_{DC}$ (test signal range 100Khz to 1Mhz) 25°C	
L_S Typical Series Inductance	3.5		nH	Measured from tab to mounting plane	
dv/dt Max. Voltage Rate of Change	10000		V/ μs	(Rated V_R)	

(1) Pulse Width < 300 μs , Duty Cycle < 2%

(2) $V_{FM} = V_{F(TO)} + r_t \times I_F$

Thermal-Mechanical Specifications

Parameters		100BGQ	Units	Conditions
T _J	Max. Junction Temperature Range	-55 to 150	°C	
T _{stg}	Max. Storage Temperature Range	-55 to 150	°C	
R _{thJC}	Max. Thermal Resistance Junction to Case	0.50	°C/W	DC operation
R _{thCS}	Typical Thermal Resistance, Case to Heatsink	0.20	°C/W	Mounting surface, smooth and greased
wt	Approximate Weight	5(0.18)	g(oz.)	
T	Mounting Torque	Min.	1.2(10)	N*m (lbf-in)
		Max.	2.4(20)	
Case Style		PowIRtab™		

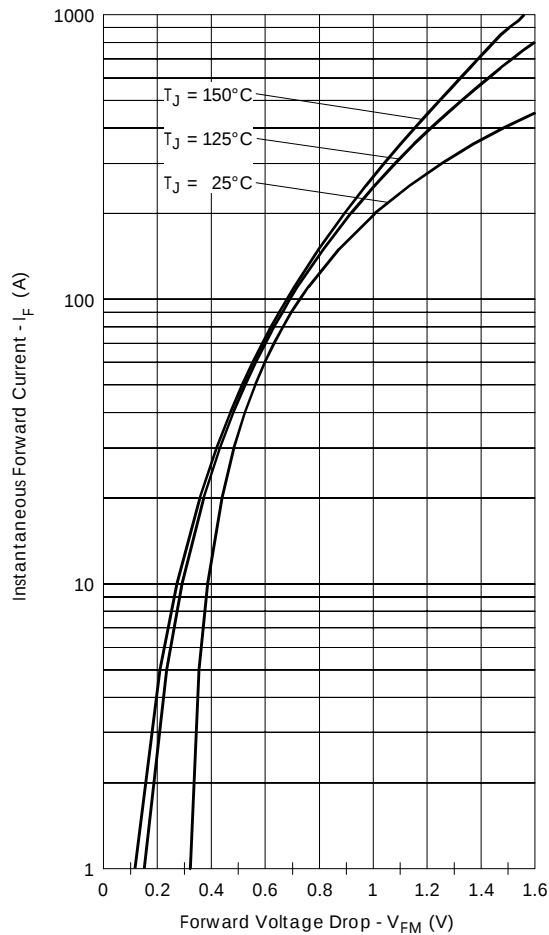


Fig. 1 - Maximum Forward Voltage Drop Characteristics

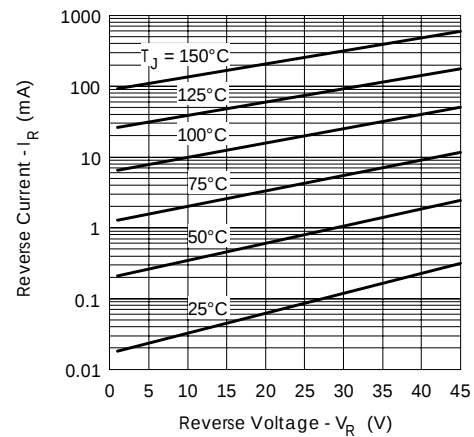


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

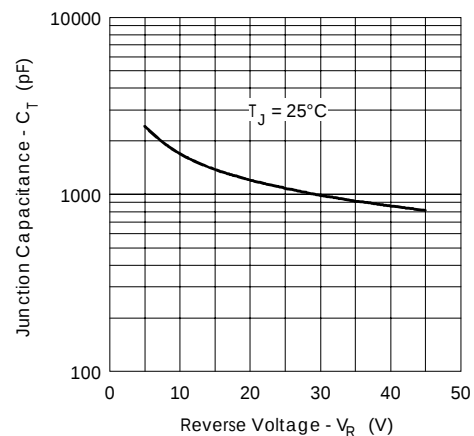


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

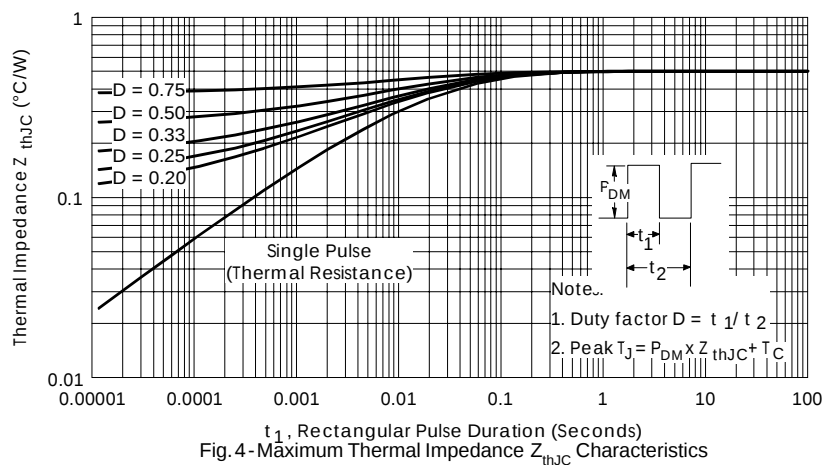


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

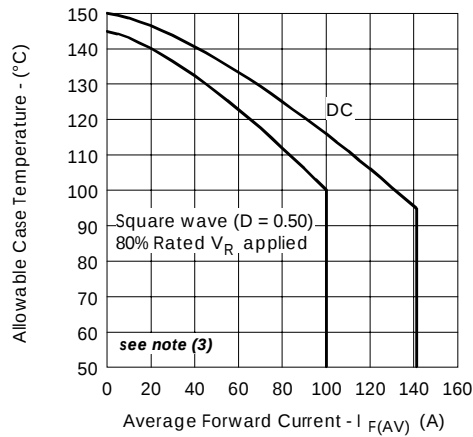


Fig. 5 - Maximum Allowable Case Temperature Vs. Average Forward Current

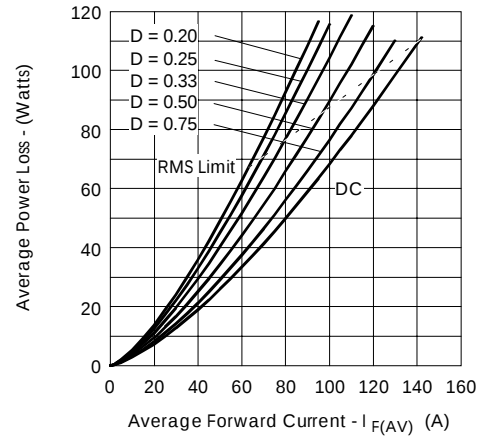


Fig. 6 - Forward Power Loss Characteristics

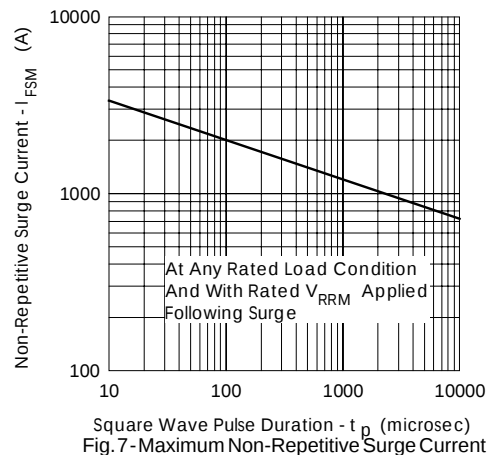


Fig. 7 - Maximum Non-Repetitive Surge Current

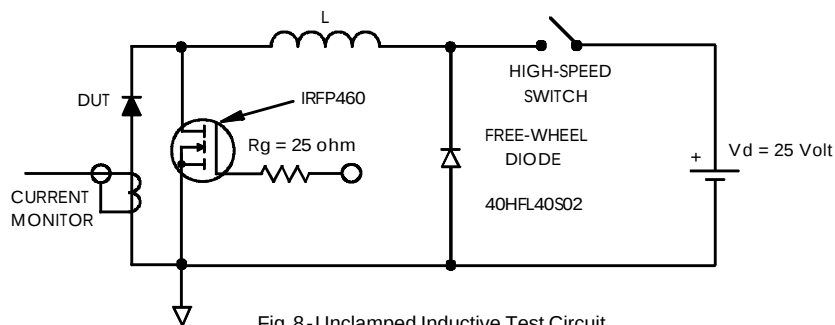


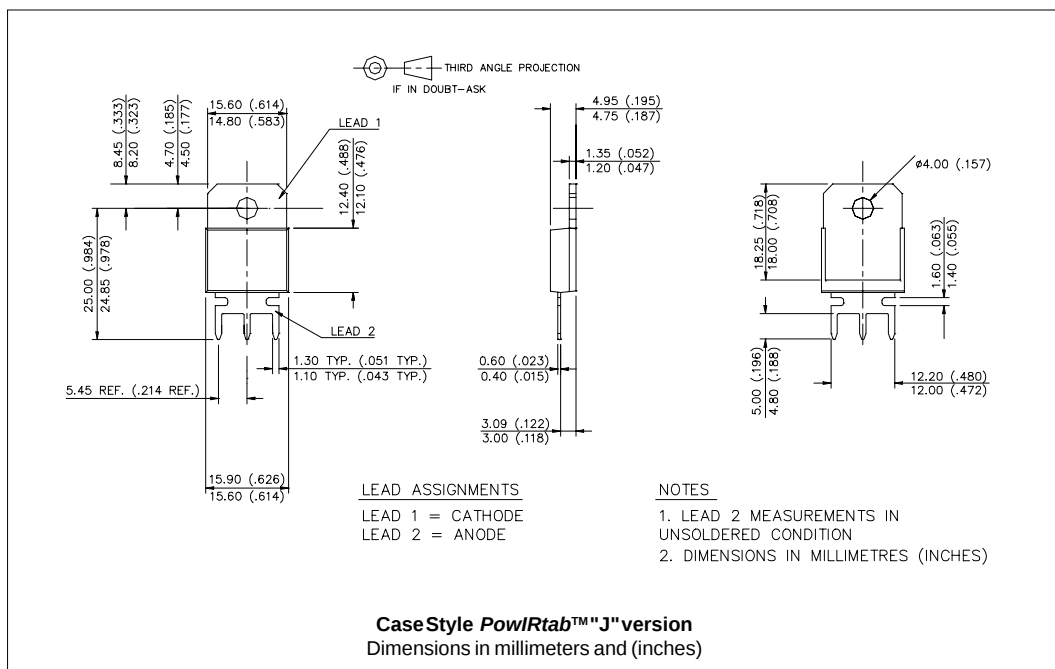
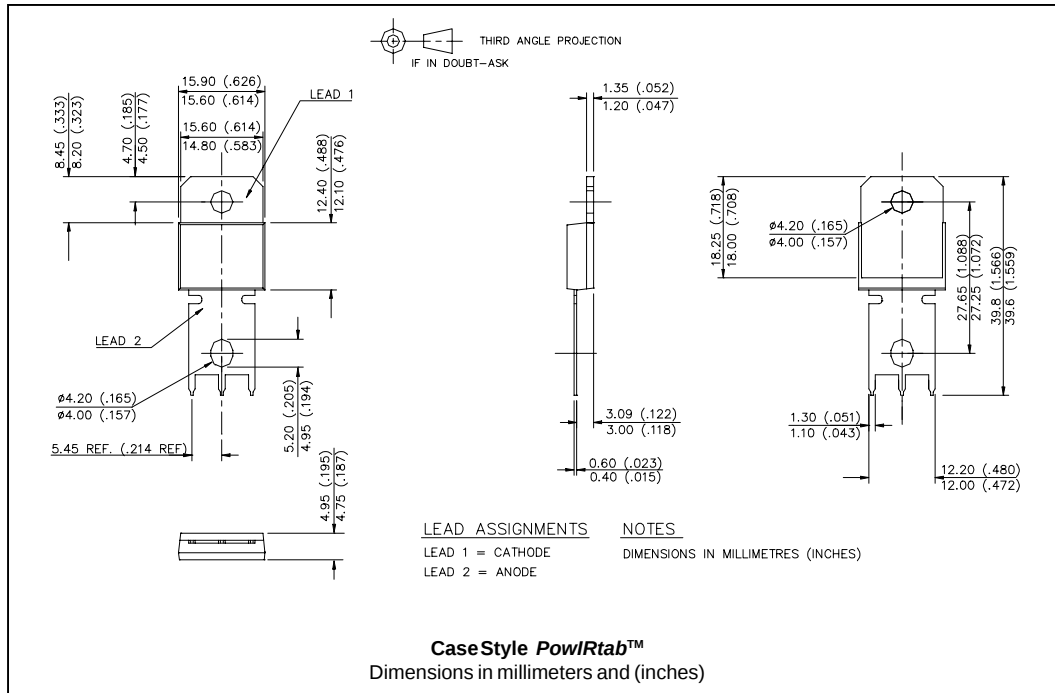
Fig. 8 - Unclamped Inductive Test Circuit

(3) Formula used: $T_c = T_j - (P_d + P_{d_{REV}}) \times R_{thJC}$;

P_d = Forward Power Loss = $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);

$P_{d_{REV}}$ = Inverse Power Loss = $V_{R1} \times I_R (1 - D)$; $I_R @ V_{R1} = 80\% \text{ rated } V_R$

Outline Table



Ordering Information Table

Device Code			
100	BGQ	045	J
①	②	③	④
1	-	Current Rating	
2	-	Essential Part Number	
3	-	Voltage code: Code = V_{RRM}	
4	-	none = PowIRtab™ standard	
	J	= Short Lead Version	

This model has been developed by
Wizard SPICE MODEL GENERATOR(1999)
(International Rectifier Corporation)
contains Proprietary Information

SPICE Model Diode is composed by a
simple diode plus paralld VCG2T

.SUBCKT 100bgq45 ANO CAT

D1 ANO 1 DMOD (0.24359)

*Define diode model

.MODEL DMOD D(IS=6.61799286342482E-05A,N=1.0212796726385,BV=45V,
+IBV=0.115140026620575A,RS=0.0005748724,CJO=3.31930927290723E-08,
+VJ=0.456112448442971,XTI=2,EG=0.721992455742664)

*Implementation of VCG2T

VX 1 2 DC 0V

R1 2 CAT TRES 1E-6

.MODEL TRES RES(R=1,TC1=9.83346387011944)

GP1 ANO CAT VALUE={-ABS(I(VX))*(EXP(((((-2.949174E-03/

9.833464)*(V(2,CAT)*1E6)/(I(VX)+1E-6)-1))+1)*6.600191E-2*ABS(V(ANO,CAT)))-1}}

.ENDS100bgq45

Thermal Model Subcircuit

.SUBCKT 100bgq45T 5 1

CTHERM1 5 4 1.66E+3

CTHERM2 4 3 2.22E+2

CTHERM3 3 2 1.48E+5

CTHERM4 2 1 3.12E+5

RTHERM1 5 4 3.42E-2

RTHERM2 4 3 2.55E-1

RTHERM3 3 2 8.41E-2

RTHERM4 2 1 1.81E-4

.ENDS 100bgq45T

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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